Features

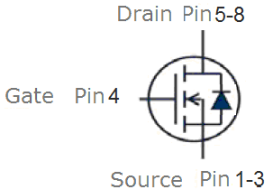
- N-Channel，5V Logic Level Control
- Enhancement mode
- Low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- Pb-free lead plating; RoHS compliant

V_{DS}	80	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	55	mΩ
$R_{DS(on),TYP}$@ V_{GS}=4.5 V	57	mΩ
I_D	18	A

PDFN3333

Pb-Free RoHS HF Halogen-Free

Part ID	Package Type	Marking	Tape and reel information
VSE080N08LS	PDFN3333	080N08L	5000PCS/Reel



Maximum ratings, at T_A =25°C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		80	V
I_S	Diode continuous forward current	T_C =25°C	18	A
I_D	Continuous drain current@VGS=10V	T_C =25°C	18	A
		T_C =100°C	11	A
I_{DM}	Pulse drain current tested ①	T_C =25°C	72	A
EAS	Avalanche energy, single pulsed ②		9	mJ
P_D	Maximum power dissipation	T_C =25°C	30	W
VGS	Gate-Source voltage		±16	V
T_{STG} T_J	Storage and operating temperature range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	4.2	°C/W
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	35	°C/W

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_j=25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	80	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_j=125℃)	V_{DS}=80V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±16V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	0.7	1.2	1.6	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=10A	--	55	70	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=4.5V, I_D=6A	--	57	72	mΩ
Dynamic Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=30V,V_{GS}=0V, f=1MHz	500	570	700	pF
C_{oss}	Output Capacitance		--	50	140	pF
C_{rss}	Reverse Transfer Capacitance		--	35	100	pF
R_g	Gate Resistance	f=1MHz	--	4.2	--	Ω
Q_g	Total Gate Charge	V_{DS}=40V,I_D=10A, V_{GS}=10V	--	11	--	nC
Q_{gs}	Gate-Source Charge		--	3.2	--	nC
Q_{gd}	Gate-Drain Charge		--	2.8	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=40V, I_D=10A, R_G=6.8Ω, V_{GS}=10V	--	7.5	--	nS
t_r	Turn-on Rise Time		--	3.5	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	22.5	--	nS
t_f	Turn-Off Fall Time		--	9	--	nS
Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=10A,V_{GS}=0V	--	0.9	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=10A, V_{GS}=0V di/dt=500A/μs	--	10	--	nS
Q_{rr}	Reverse Recovery Charge			15		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 6A, V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

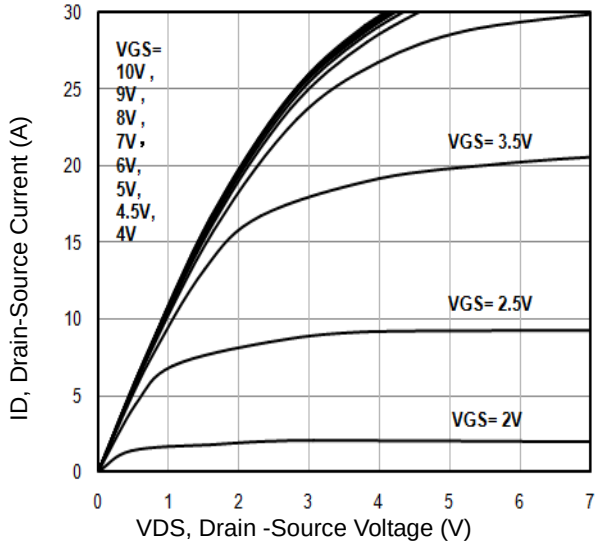


Fig1. Typical Output Characteristics

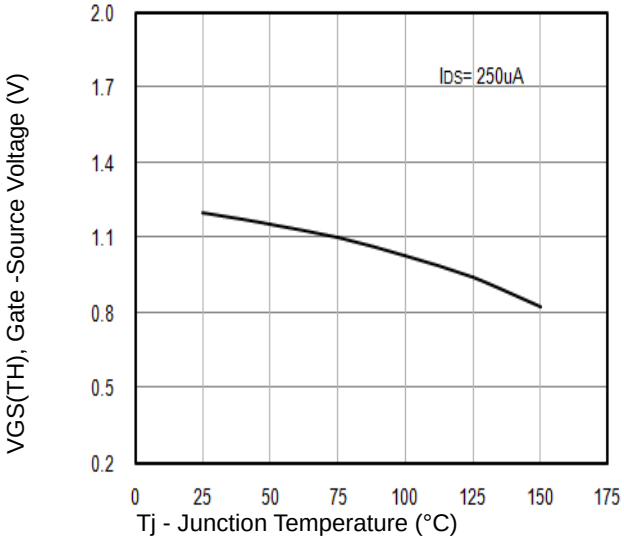


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs.Tj

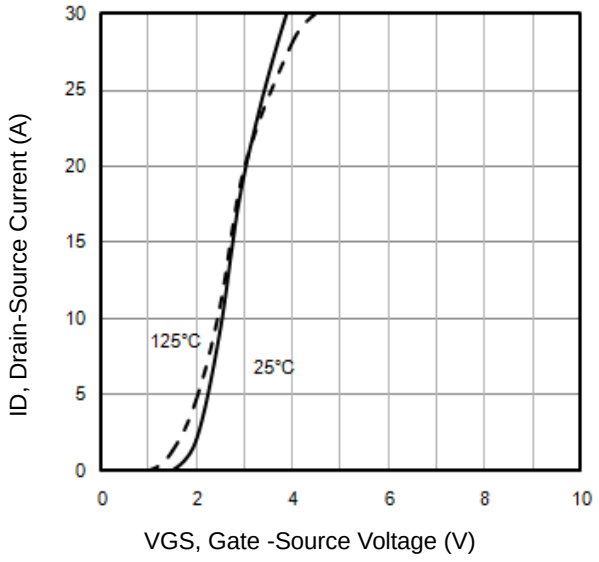


Fig3. Typical Transfer Characteristics

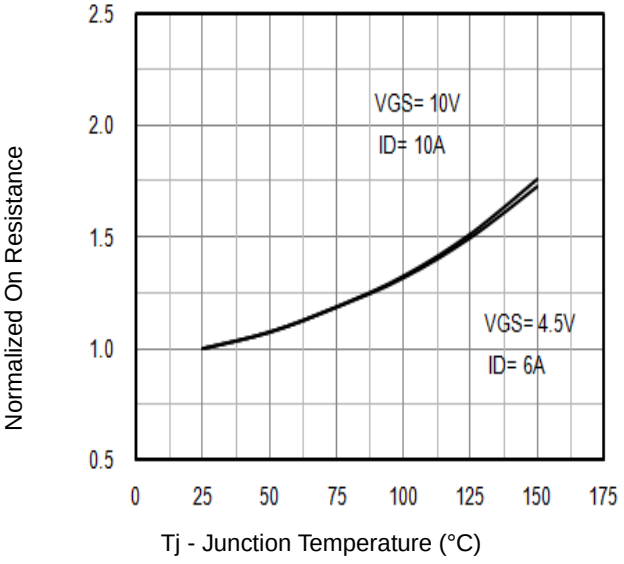


Fig4. Normalized On-Resistance Vs. Tj

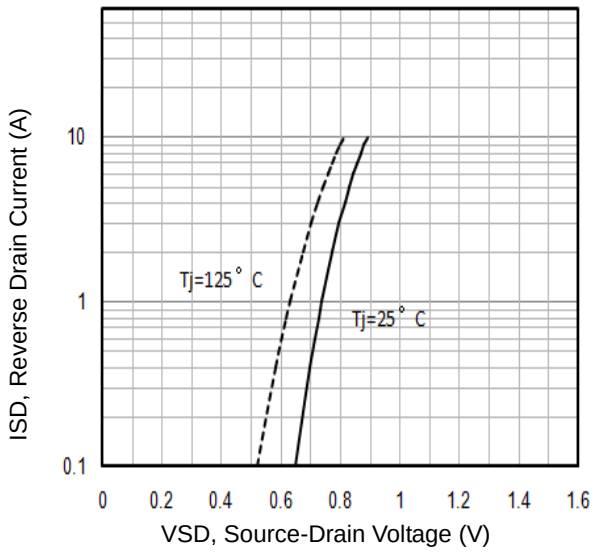


Fig5. Typical Source-Drain Diode Forward Voltage

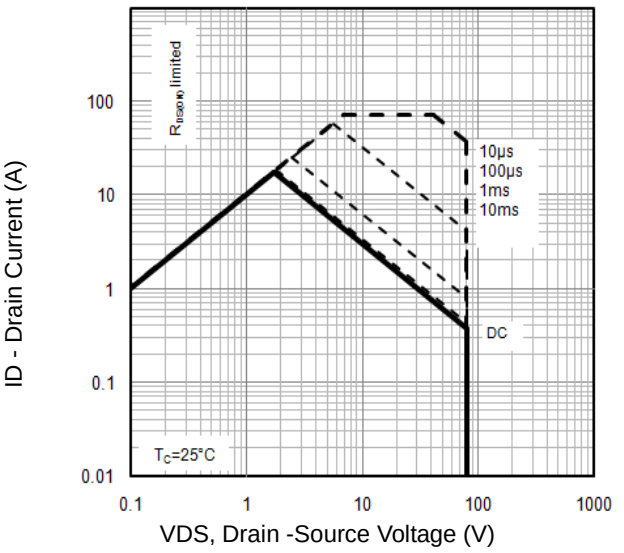


Fig6. Maximum Safe Operating Area

Typical Characteristics

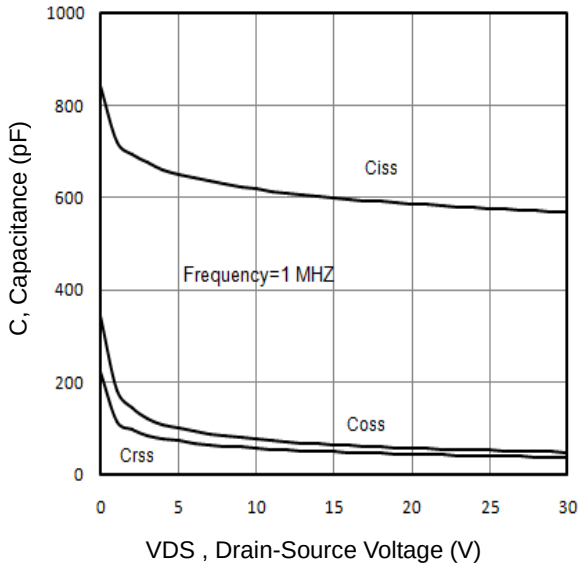


Fig7. Typical Capacitance Vs.Drain-Source Voltage

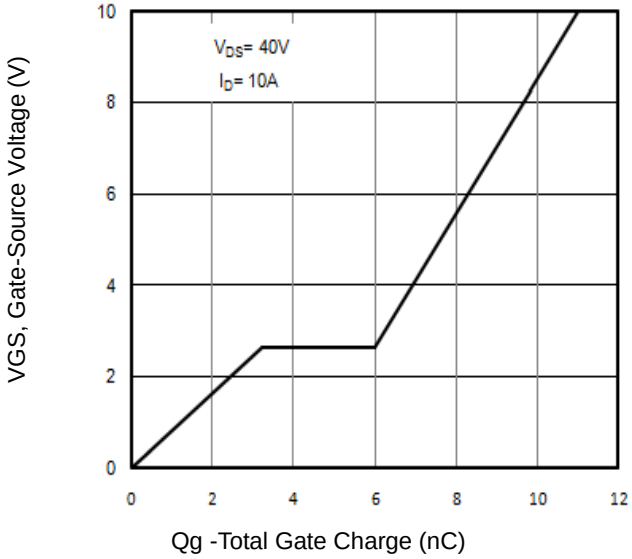


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

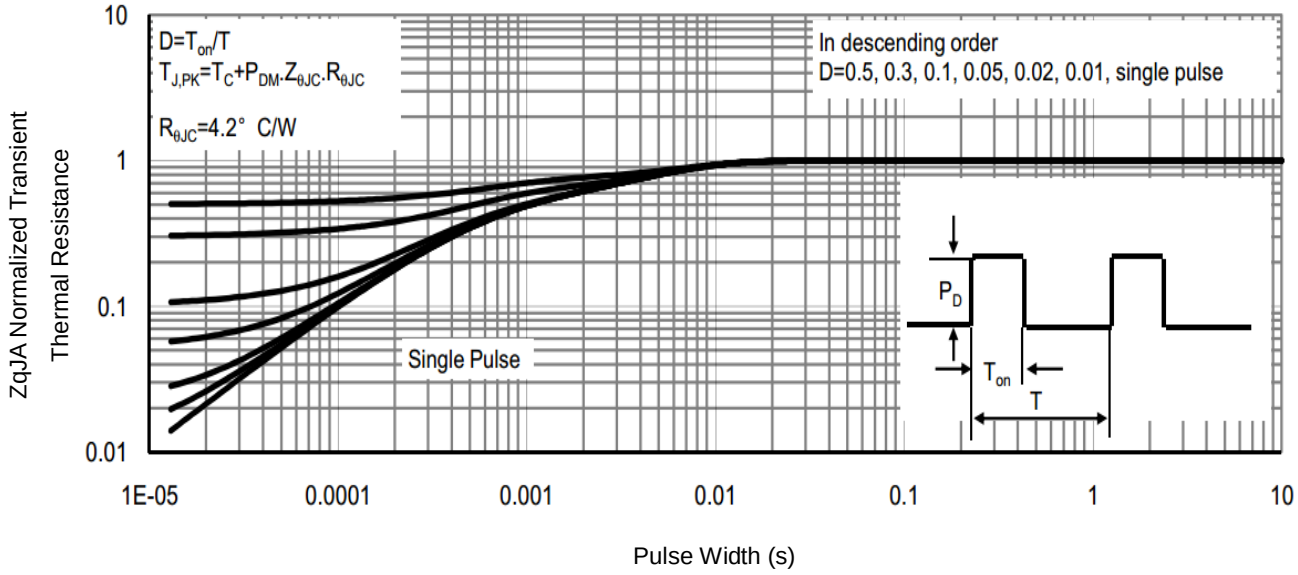


Fig9. Normalized Maximum Transient Thermal Impedance

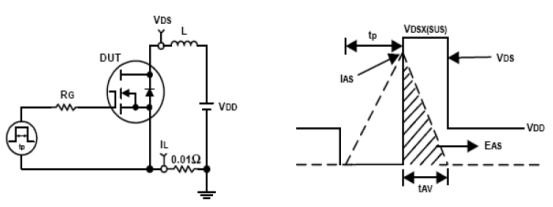


Fig10. Unclamped Inductive Test Circuit and waveforms

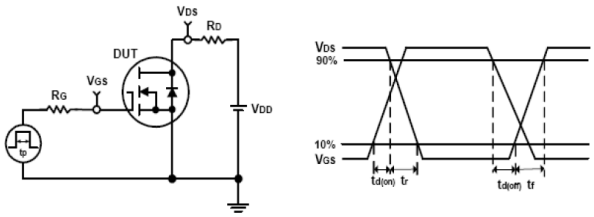
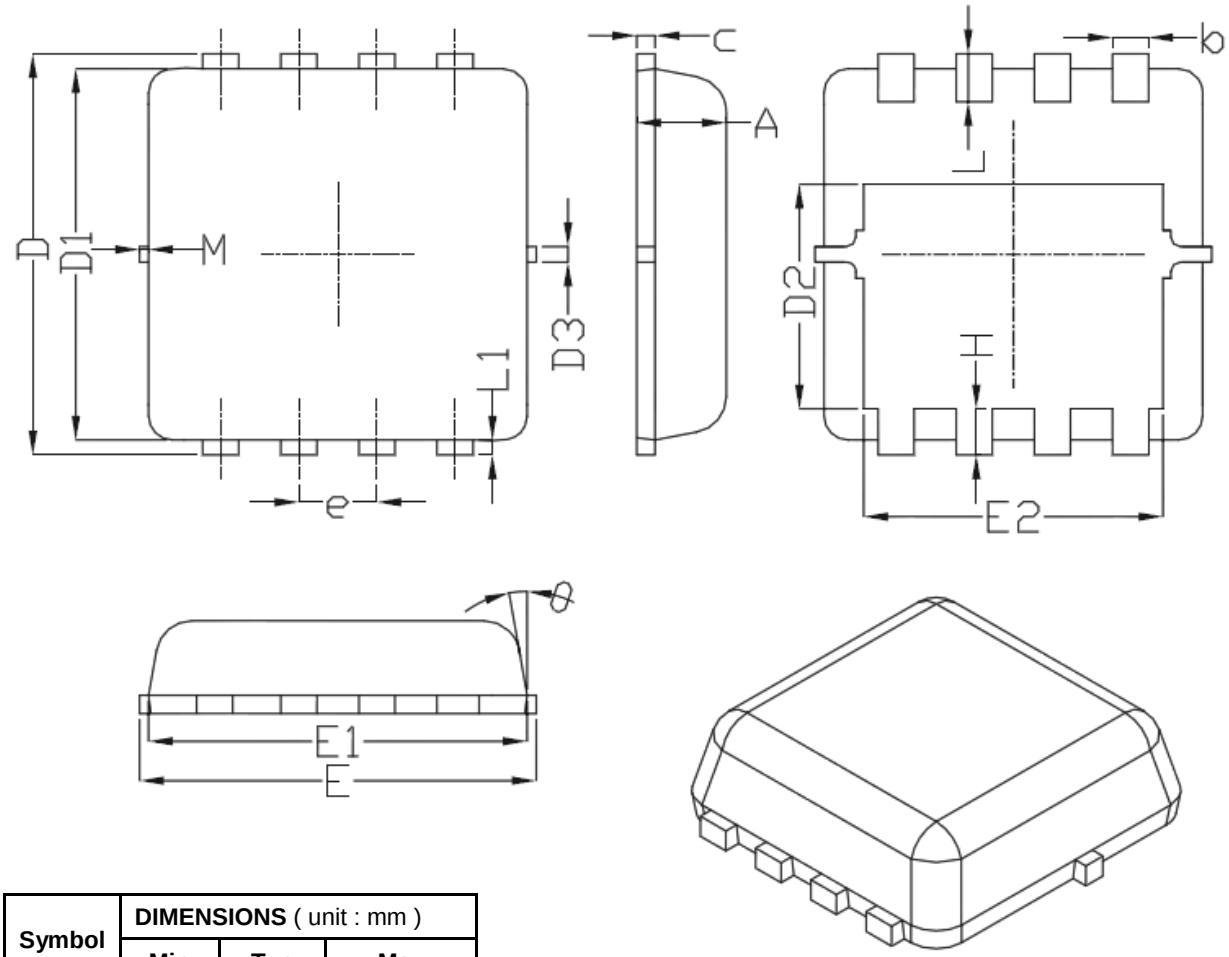


Fig11. Switching Time Test Circuit and waveforms

PDFN3333 Package Outline Data



Symbol	DIMENSIONS (unit : mm)		
	Min	Typ	Max
A	0.7	0.75	0.8
b	0.25	0.3	0.35
C	0.1	0.15	0.25
D	3.25	3.35	3.45
D1	3	3.1	3.2
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.2	3.3	3.4
E1	3	3.15	3.2
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.3	0.39	0.5
L	0.3	0.4	0.5
L1	--	0.13	--
θ	--	10°	12°
M	*	*	0.15
* Not specified			

Notes:

1. Follow JEDEC MO-240 variation CA.
2. Dimensions "D1" and "E1" do NOT include mold flash protrusions or gate burrs.
3. Dimensions "D1" and "E1" include interterminal flash or protrusion. Interterminal flash or protrusion shall not exceed 0.25mm per side.

Customer Service

Sales and Service:
sales@vgsemi.com

Vanguard Semiconductor CO., LTD
TEL: (86-755) -26902410
FAX: (86-755) -26907027
WEB: www.vgsemi.com